

**isc N-Channel MOSFET Transistor**

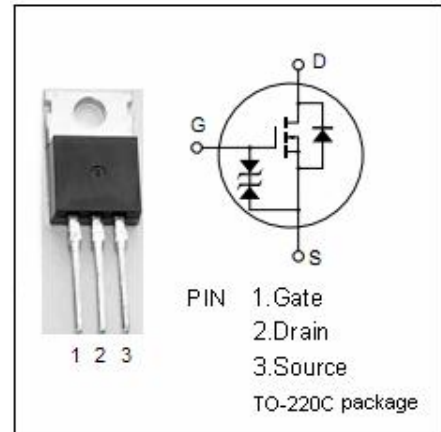
**2SK2389**

**DESCRIPTION**

- Drain Current  $I_D = 5A @ T_C = 25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS} = 700V(\text{Min})$
- Fast Switching Speed

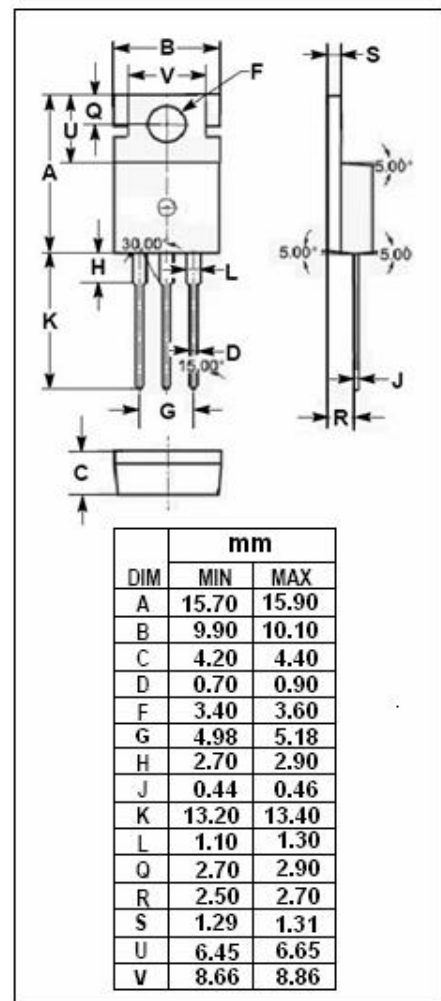
**APPLICATIONS**

- Switching regulators



**ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ C$ )**

SYMBOL	ARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	700	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current-continuous@ $T_C = 25^\circ C$	5	A
$P_{tot}$	Total Dissipation@ $T_C = 25^\circ C$	125	W
$T_j$	Max. Operating Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



**isc N-Channel Mosfet Transistor****2SK2389**• ELECTRICAL CHARACTERISTICS ( $T_C=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=1\text{mA}$	700			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=1\text{mA}$	1.5		3.5	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}; I_D=2.0\text{A}$			1.7	$\Omega$
$I_{GSS}$	Gate-Body Leakage Current	$V_{GS}= \pm 30\text{V}; V_{DS}=0$			$\pm 100$	nA
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=700\text{V}; V_{GS}=0$			500	$\mu\text{A}$